

MOS FIELD EFFECT TRANSISTOR μ PA2503

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA2503, which has a heat spreader, is N-channel MOS Field Effect Transistor designed for power management applications of notebook computers.

FEATURES

- μ PA2503 has a thin surface mount package with a heat spreader. The land size is same as 8-pin TSSOP.
- Low on-state resistance

 $R_{DS(on)1}$ = 9.5 m Ω MAX. (VGS = 10.0 V, ID = 8.0 A)

 $R_{DS(on)2} = 15.1 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 4.5 \text{ V, Ip} = 8.0 \text{ A)}$

• Low Ciss: 1200 pF TYP. (VDS = 10.0 V, VGS = 0 V)

ORDERING INFORMATION

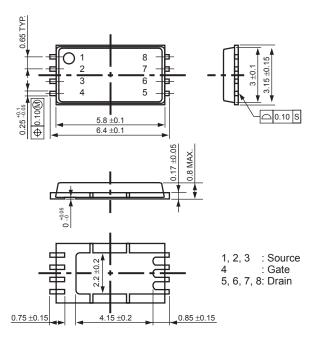
PART NUMBER	PACKAGE
μ PA2503TM	8PIN HWSON

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

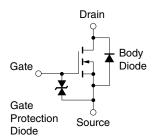
VDSS	30.0	V	
Vgss	±20.0	V	
I _{D(DC)}	±16.0	Α	
ID(pulse)	±64.0	Α	
Рт	2.7	W	
Tch	150	°C	
Tstg	-55 to +150	°C	
las	16.0	Α	
Eas	25.6	mJ	
	VGSS ID(DC) ID(pulse) PT Tch Tstg IAS	VGSS ±20.0 ID(DC) ±16.0 ID(pulse) ±64.0 PT 2.7 Tch 150 Tstg -55 to +150 IAS 16.0	

- **Notes 1.** Mounted on FR-4 board of 25 cm² x 1.6 mm, PW \leq 10 sec
 - **2.** PW \leq 10 μ s, Duty Cycle \leq 1%
 - 3. Starting T_{ch} = 25°C, V_{DD} = 30 V, R_G = 25 Ω , V_{GS} = 20.0 \rightarrow 0 V

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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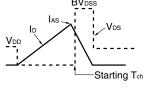
ELECTRICAL CHARACTERISTICS (TA = 25°C)

DataSheeCHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30.0 V, V _{GS} = 0 V			1.0	μΑ
Gate Leakage Current	Igss	V _{GS} = ±18.0 V, V _{DS} = 0 V			±10.0	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10.0 V, I _D = 1.0 mA	1.5		2.5	V
Forward Transfer Admittance Note	y fs	V _{DS} = 10.0 V, I _D = 8.0 A	5			S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10.0 V, I _D = 8.0 A		7.5	9.5	mΩ
	RDS(on)2	V _{GS} = 4.5 V, I _D = 8.0 A		11.0	15.1	mΩ
Input Capacitance	Ciss	V _{DS} = 10.0 V		1200		pF
Output Capacitance	Coss	V _{GS} = 0 V		320		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		190		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15.0 V, I _D = 8.0 A		12		ns
Rise Time	tr	V _{GS} = 10.0 V		17		ns
Turn-off Delay Time	$t_{\sf d(off)}$	R _G = 10 Ω		52		ns
Fall Time	tf			15		ns
Total Gate Charge	Q G	V _{DD} = 15.0 V		15		nC
Gate to Source Charge	Qgs	V _{GS} = 5.0 V		4		nC
Gate to Drain Charge	Q _{GD}	I _D = 16.0 A		7		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 16.0 A, V _{GS} = 0 V		0.84		V
Reverse Recovery Time	trr	IF = 16.0 A, VGS = 0 V		28		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		18		nC

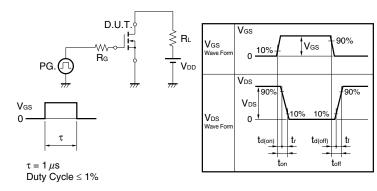
Note Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2%

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ $PG. \bigcirc PG. \bigcirc PG.$



TEST CIRCUIT 2 SWITCHING TIME

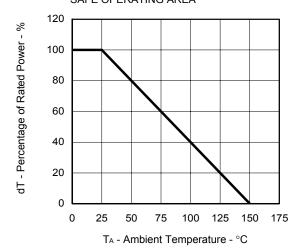


TEST CIRCUIT 3 GATE CHARGE

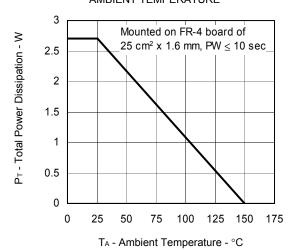
$$\begin{array}{c|c} D.U.T. \\ \hline I_G = 2 \text{ mA} \\ \hline \hline WV \circ U \end{array} \begin{array}{c} \\ \hline \\ \hline \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \end{array} \begin{array}{$$

TYPICAL CHARACTERISTICS (TA = 25°C)

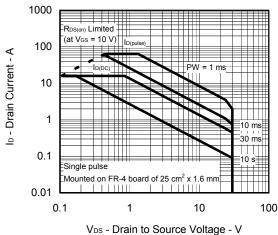
www.DataShee DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



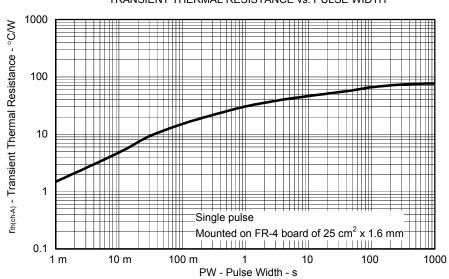
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



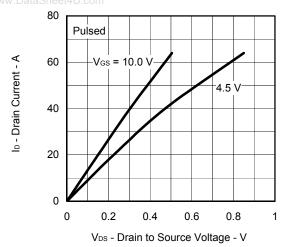
FORWARD BIAS SAFE OPERATING AREA



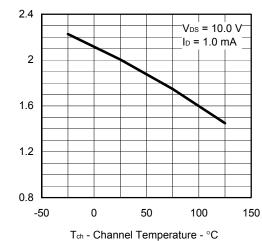




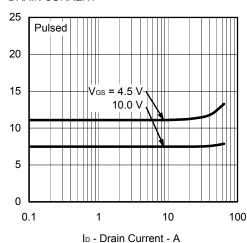
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



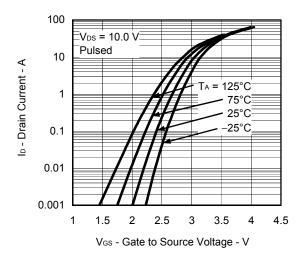
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



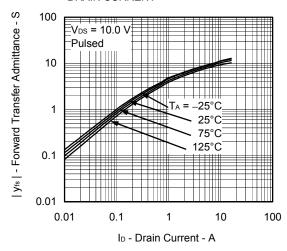
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



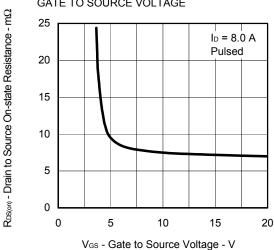
FORWARD TRANSFER CHARACTERISTICS



FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



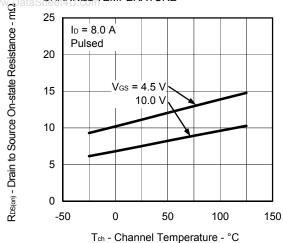
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



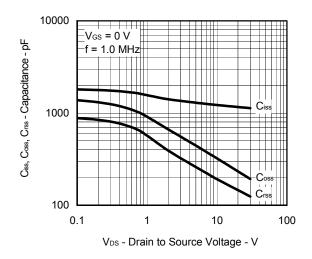
R_{DS(on)} - Drain to Source On-state Resistance - mΩ

VGS(off) - Gate Cut-off Voltage - V

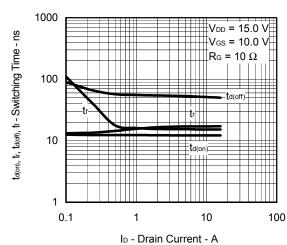
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



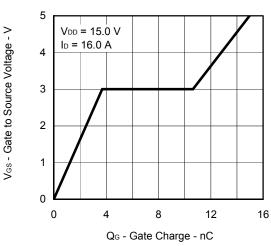
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



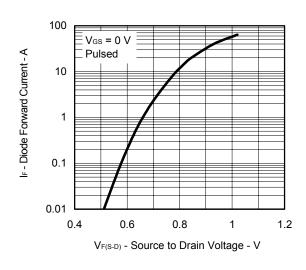
SWITCHING CHARACTERISTICS



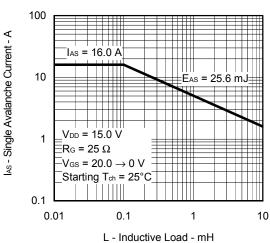
DYNAMIC INPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



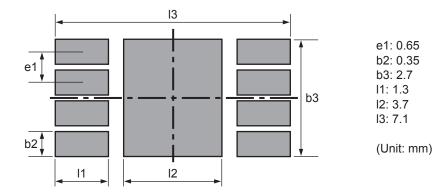
SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



EXAMPLE OF THE LAND PATTERN

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Please optimize the land pattern in consideration of density, appearance of solder fillets, common difference, etc in an actual design.



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